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(54) **CONDUCTIVE SUBSTRUCTURES OF A MULTILAYERED LAMINATE**

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(52) **U.S. Cl.** **174/255**; 174/262; 29/846; 29/852; 361/780

(58) **Field of Search** 174/262, 255; 361/780, 778, 761; 29/846, 852

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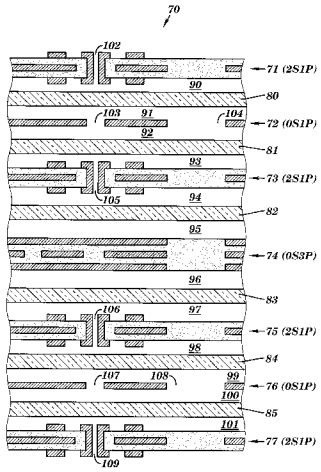
(57) **ABSTRACT**

Conductive substructures of a multilayered laminate and associated methods of fabrication. The conductive substructures include a 0S1P substructure, a 0S3P substructure, and a 2S1P substructure, in accordance with the notation nSmP, wherein n and m are non-negative integers, wherein S stands for "signal plane," and wherein P stands for "power plane." A signal plane is characterized by its inclusion of a layer comprising conductive circuitry. A power plane is characterized by its inclusion of a continuously conductive layer. Thus, a 0S1P substructure includes 0 signal planes and 1 power plane (n=0, m=1). A 0S3P substructure includes 0 signal planes and 3 power plane (n=0, m=3) with a dielectric layer between each pair of power planes. A 2S1P substructure includes 2 signal planes and 1 power plane (n=2, m=1) with a dielectric layer between the power plane and each signal plane. A multilayered laminate includes a stacked substructure configuration having any combination of 0S1P, 0S3P, and 2S1P substructures with dielectric material insulatively separating the substructures from one another.

3 Claims, 7 Drawing Sheets



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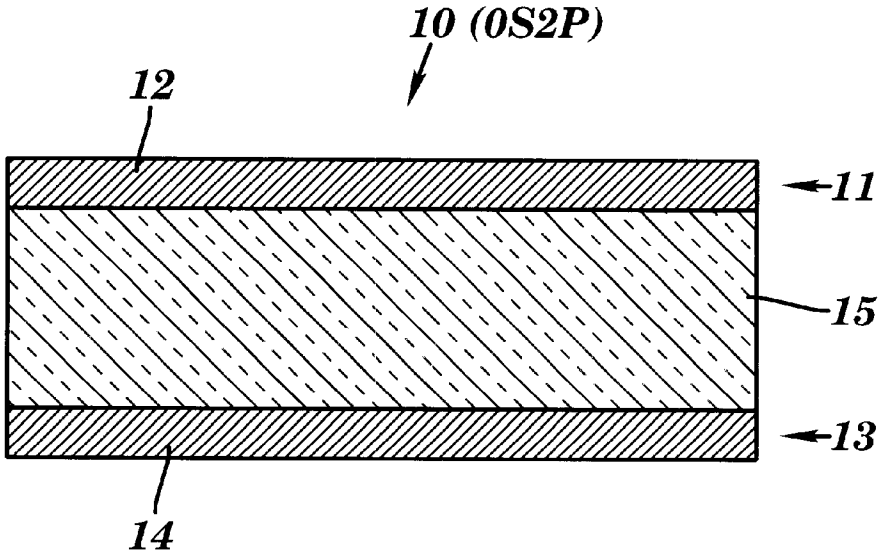


FIG. 1
(RELATED ART)

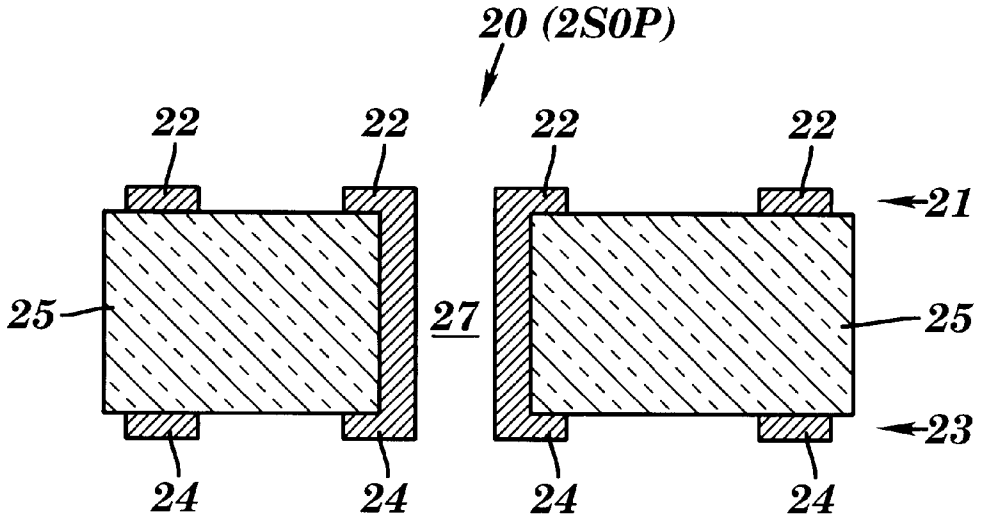


FIG. 2
(RELATED ART)

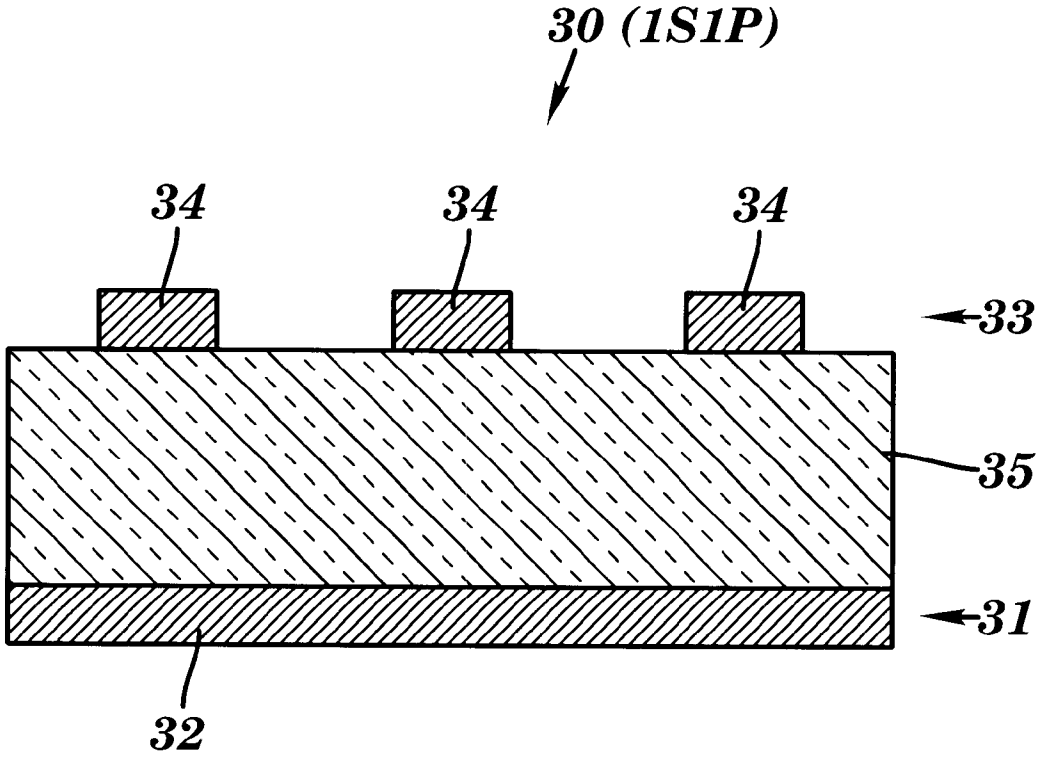
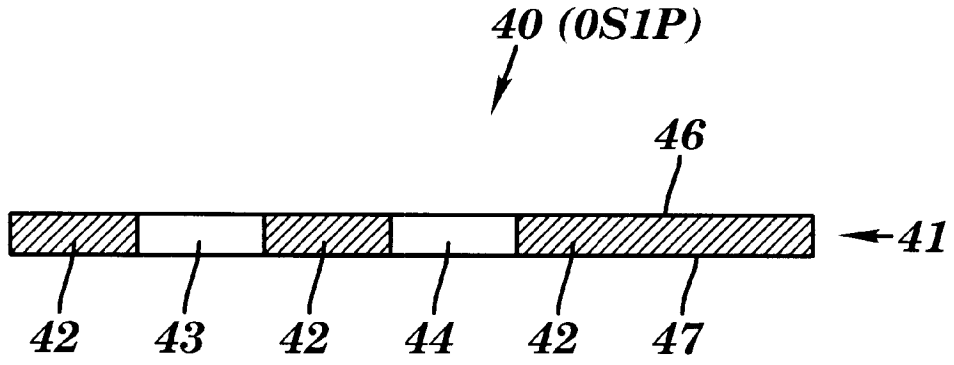


FIG. 3
(RELATED ART)


40 (0S1P)
46
41
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42
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FIG. 4

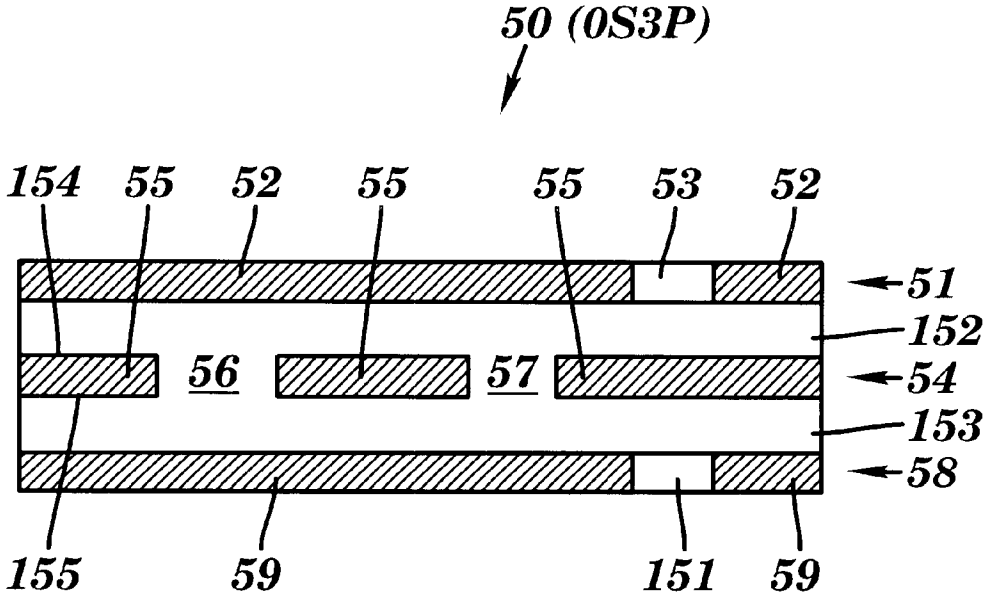
50 (0S3P)
154
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FIG. 5

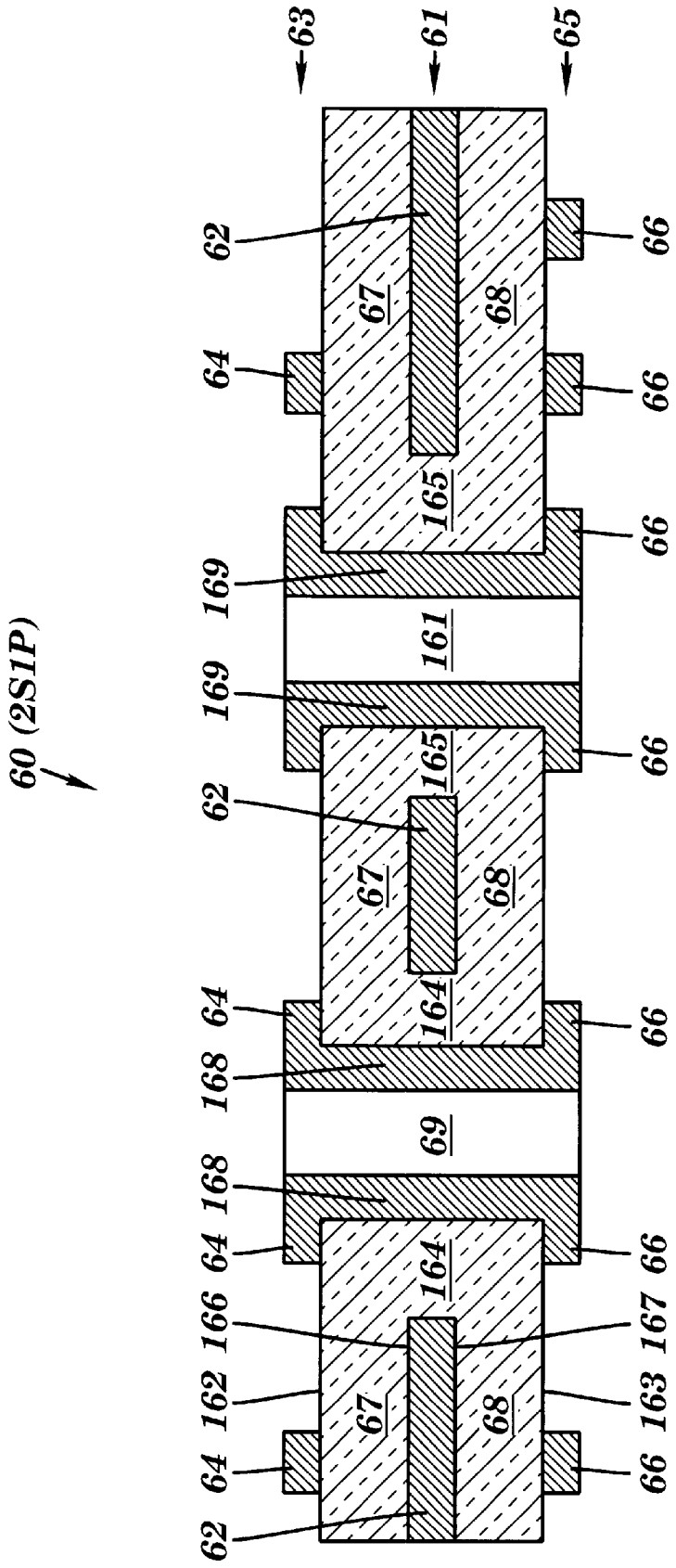
60 (2S1P)
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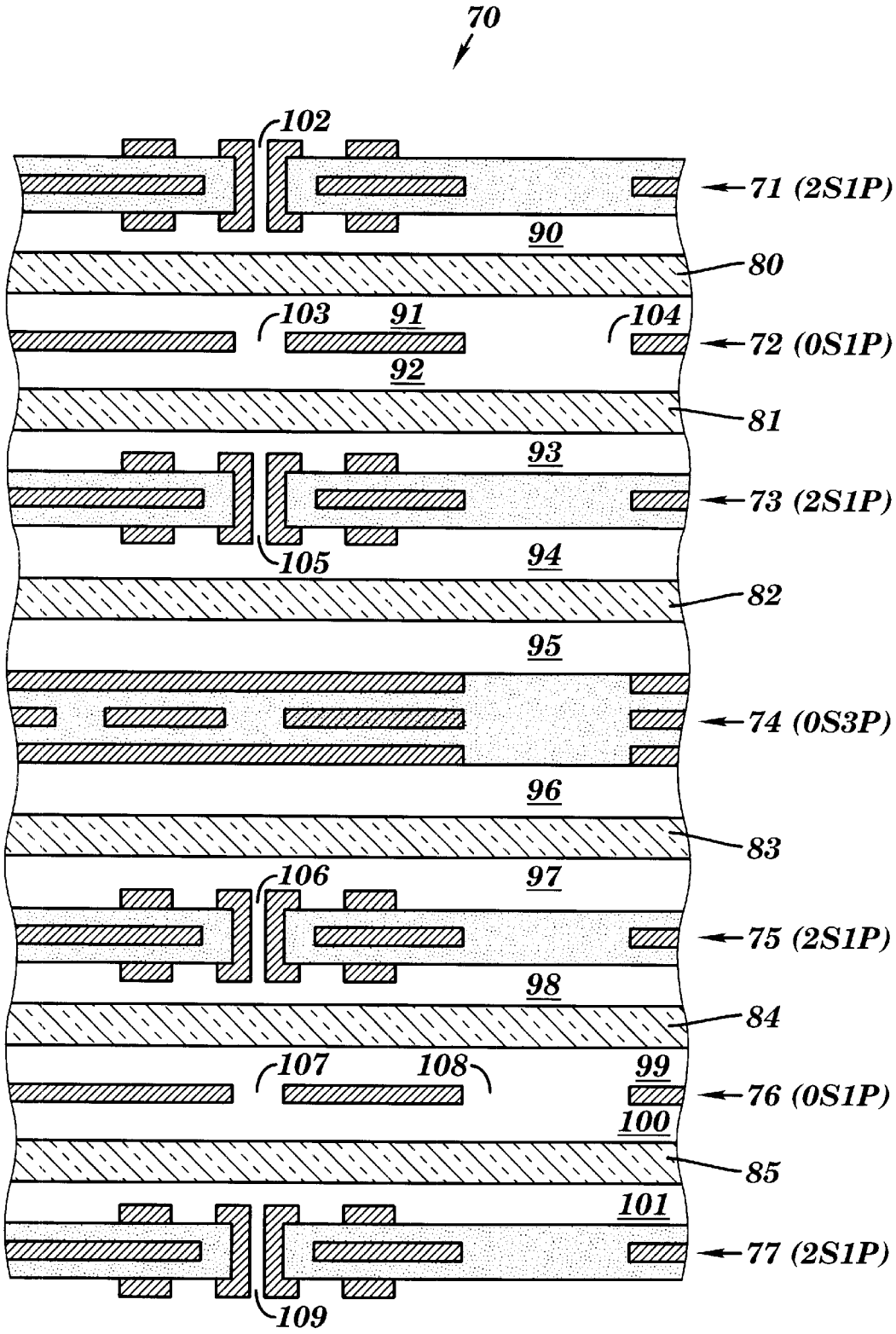
FIG. 6


70
102
71 (2S1P)
90
80
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91
104
72 (0S1P)
92
81
93
73 (2S1P)
105
94
82
95
74 (0S3P)
96
83
106
97
75 (2S1P)
98
84
107
108
99
76 (0S1P)
100
85
101
77 (2S1P)
109

FIG. 7

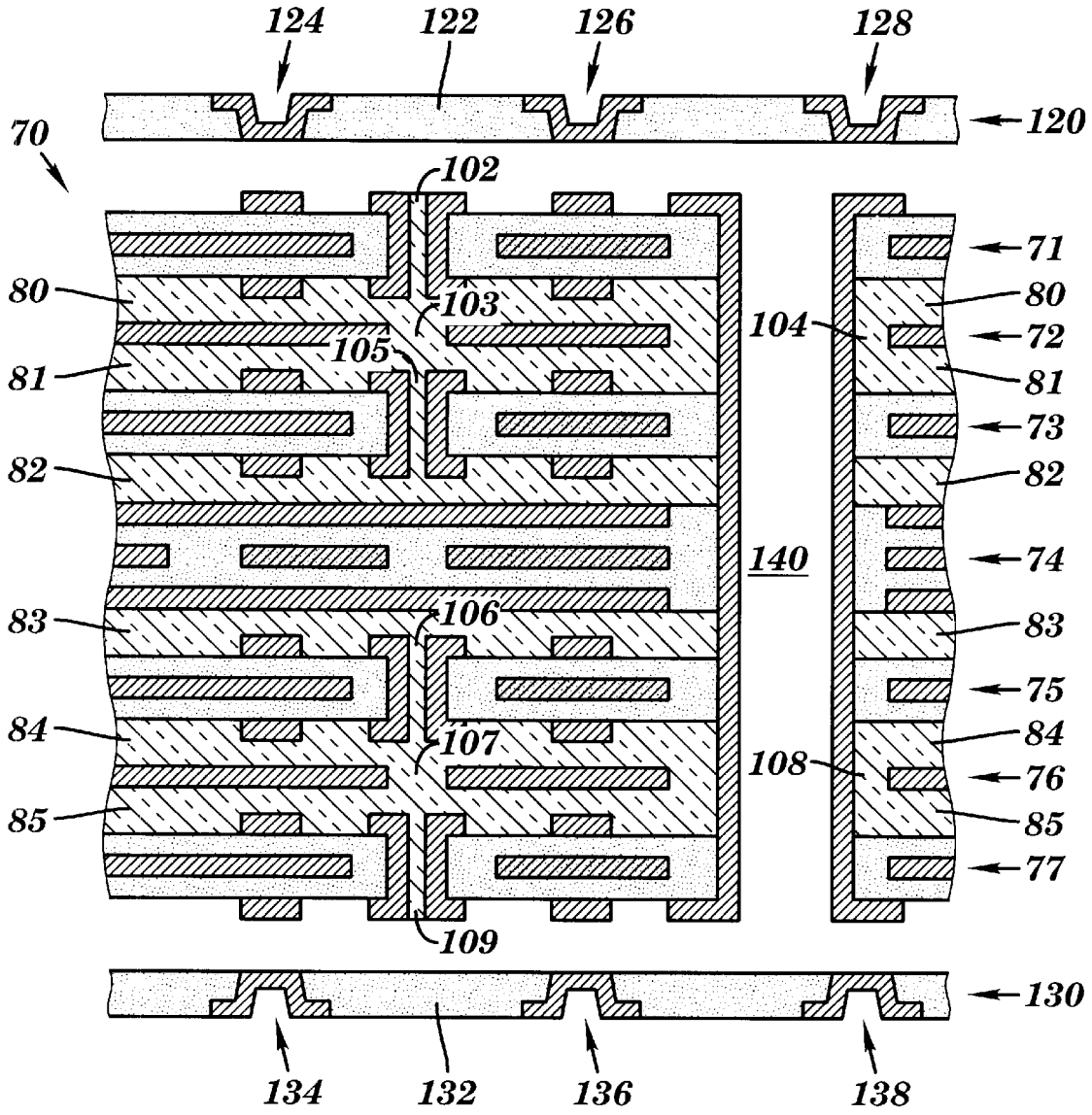
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FIG. 8

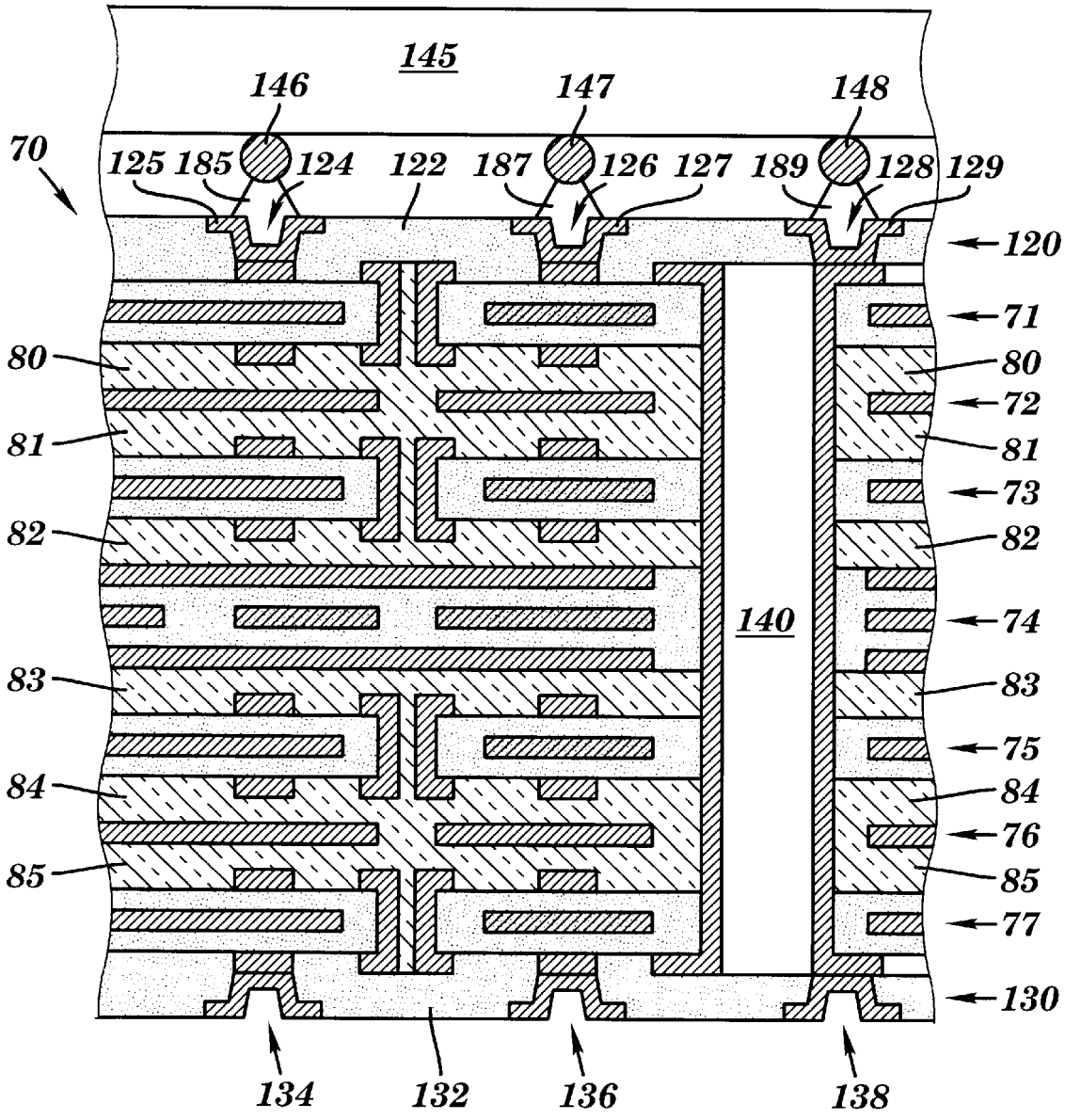
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FIG. 9

CONDUCTIVE SUBSTRUCTURES OF A MULTILAYERED LAMINATE

BACKGROUND OF THE INVENTION

1. Technical Field

The present invention relates to conductive substructures of a multilayered laminate and associated methods of fabrication.

2. Related Art

FIGS. **1**, **2**, and **3** illustrate conductive substructures that may appear in a conventional multilayered laminate. FIG. **1** illustrates a 0S2P substructure **10**, FIG. **2** illustrates a 2S0P substructure **20**, and FIG. **3** illustrates a 1S1P substructure **30**. Definitionally, the substructures in this application are described by an adjective of the form nSmP, wherein n and m are non-negative integers, wherein S stands for "signal plane," and wherein P stands for "power plane." Thus, "0S2P" connotes 0 signal planes and 2 power planes (n=0, m=2), "2S0P" connotes 2 signal planes and 0 power planes (n=2, m=0), and "1S1P" connotes 1 signal plane and 1 power plane (n=1, m=1). A conventional multilayered laminate comprises stacked substructures which may include any or all of the 0S2P, 2S0P, and 1S1P substructures.

A power plane is characterized by its inclusion of a continuously conductive layer. For example, the 0S2P substructure **10** in FIG. **1** comprises a power plane **11** which includes a continuously conductive layer **12**, and a power plane **13** which includes a continuously conductive layer **14**. As another example, the 1S1P substructure **30** in FIG. **3** comprises a power plane **31** which includes a continuously conductive layer **32**. Although not shown in FIGS. **1** and **3**, a power plane may include one or more holes within the continuous conductive layer. The continuous conductive layer of a power plane may include copper.

A signal plane is characterized by its inclusion of a layer comprising conductive circuitry. For example, the 2S0P substructure **20** in FIG. **2** comprises a signal plane **21** which includes a conductive circuitry **22**, and a signal plane **23** which includes a conductive circuitry **24**. As another example, the 1S1P substructure **30** in FIG. **3** comprises a signal plane **33** which includes a conductive circuitry **34**. The conductive circuitry of a signal plane may include copper.

A substructure may include a via through its thickness, such as a conductively plated via **27** in the 2S0P substructure **20** in FIG. **2**.

In a substructure, a power plane cannot conductively contact another power plane, a power plane cannot conductively contact a signal plane, and a signal plane cannot conductively contact another signal plane. Thus, power planes and signal planes may be insulatively separated by a dielectric layer. As a first example, the 0S2P substructure **10** in FIG. **1** comprises a dielectric layer **15** that insulatively separates the power plane **11** from the power plane **13**. As a second example, the 2S0P substructure **20** in FIG. **2** comprises a dielectric layer **25** that insulatively separates the signal plane **21** from the signal plane **23**. As a third example, the 1S1P substructure **30** in FIG. **3** comprises a dielectric layer **35** that insulatively separates the power plane **31** from the signal plane **33**.

Unfortunately, some or all of the preceding 0S2P, 2S0P, and 1S1P substructures prevent improved wiring density within the substructures, and thus within the overall multilayered laminate that includes the 0S2P, 2S0P, and 1S1P substructures. With the 2S0P substructure of FIG. **2**, for example, the conductive circuitry **22** may be required to be oriented at about right angles to the conductive circuitry **24** in order to minimize cross-talk (i.e., noise) due to electromagnetic radiative coupling between the conductive circuitry **22** and the conductive circuitry **24**; i.e., if x and y axes represent orthogonal directions within the signal planes **21** and **23**, then the conductive circuitry **22** would be oriented in the x direction if the conductive circuitry **24** were oriented in the y direction, and vice versa. The aforementioned directional constraints on the conductive circuitry **22** and the conductive circuitry **24** translates into a constraint on wireability (i.e., a constraint on how high the wiring density can be within the signal planes **21** and **23**).

Additionally, with less than optimum wiring density, the geometrical size of the overall multilayered laminate will have to be large enough to accommodate all of the wiring that is physically required for the intended application. The increased size is undesirable, because of at least two reasons. A first reason is that space is likely to be at a premium and a conservation of space is generally strived for in the electronic packaging industry. A second reason is that an increased size is more expensive because of increased material requirements and, more importantly, a requirement to drill longer through holes through the substructures and the overall multilayered laminate.

Moreover, if a highly pliable or flexible dielectric material is used in the substructures, then all three of the 0S2P, 2S0P, and 1S1P substructures will be required to have a thickness that is large enough for the substructures to have sufficient structural rigidity. Note that an organic dielectric material for use in a chip carrier may exemplify a highly pliable or flexible dielectric.

There is a need for conductive substructures for use in multilayered laminates such as chip carriers, wherein the conductive substructures improve wireability, reduce substructure and overall laminate thicknesses, and result in lower fabrication costs.

SUMMARY OF THE INVENTION

The present invention provides a method for forming a 0S1P substructure, comprising:

- providing a sheet of conductive material with an exposed first surface and an exposed second surface;
- forming a hole through the sheet of conductive material; and
- applying a layer of dielectric material to the exposed first surface after the step of forming a hole.

The present invention provides a method for forming a 0S3P substructure, comprising

- providing a sheet of conductive material having an exposed first surface and an exposed second surface;
- forming a hole through the sheet of conductive material;
- applying a first layer of dielectric material to the first surface of the sheet of conductive material, after the step of forming a hole;
- applying a second layer of dielectric material to the second surface of the sheet of conductive material, after the step of forming a hole;
- applying a first layer of conductive material on the first layer of dielectric material; and
- applying a second layer of conductive material on the second layer of dielectric material.

The present invention provides a method for forming a 2S1P substructure, comprising:

- providing a sheet of conductive material having an exposed first surface and an exposed second surface;

forming a hole through the sheet of conductive material;

applying a first layer of dielectric material to the first surface of the sheet of conductive material, after the step of forming a hole;

forming a first signal plane on the first layer of dielectric material;

applying a second layer of dielectric material to the second surface of the sheet of conductive material, after the step of forming a hole; and

forming a second signal plane on the second layer of dielectric material.

The present invention provides an electrical structure, comprising: a multilayered laminate that includes a plurality of substructures, wherein a dielectric material of a dielectric layer insulatively separates each pair of successive substructures, and wherein a subset of the plurality of substructures is selected from the group consisting of a 0S1P substructure and a 0S3P substructure, the 0S1P substructure and a 2S1P substructure, the 0S3P substructure and the 2S1P substructure, the 0S1P substructure and the 0S3P substructure and the 2S1P substructure, and the 0S3P substructure.

The present invention provides a 0S3P substructure, comprising:

a sheet of conductive material having a hole therethrough;

a first layer of dielectric material on a first surface of the sheet of conductive material;

a second layer of dielectric material on a second surface of the sheet of conductive material;

a first layer of conductive material on the first layer of dielectric material, said first layer of conductive material having a hole therethrough; and

a second layer of conductive material on the second layer of dielectric material, said second layer of conductive material having a hole therethrough.

The present invention has the advantages of improving wireability, reducing substructure and overall laminate thicknesses, and resulting in lower fabrication costs. In particular, the power plane of the 2S1P substructure of the present invention serves as a shielding layer that eliminates the cross-talk that may occur with the 2S0P substructure of the related art. Thus the power plane of the 2S1P substructure improves wireability and conserves space. Additionally, the interior power plane of the 0S1P, 0S3P, 2S1P substructures of the present invention provides added structural rigidity that makes it possible to reduce the thickness of these substructures, especially if these substructures include a highly pliable or flexible dielectric material such as may characterize an organic dielectric material.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. **1** depicts a front cross sectional view of a 0S2P substructure, in accordance with the related art.

FIG. **2** depicts a front cross sectional view of a 2S0P substructure, in accordance with the related art.

FIG. **3** depicts a front cross sectional view of a 1S1P substructure, in accordance with the related art.

FIG. **4** depicts a front cross sectional view of a 0S1P substructure, in accordance with preferred embodiments of the present invention.

FIG. **5** depicts a front cross sectional view of a 0S3P substructure, in accordance with preferred embodiments of the present invention.

FIG. **6** depicts a front cross sectional view of a 2S1P substructure, in accordance with preferred embodiments of the present invention.

FIG. **7** depicts a multilayered laminate that includes 0S1P, 0S3P, and 2S1P substructures, in accordance with preferred embodiments of the present invention.

FIG. **8** depicts the multilayered laminate of FIG. **7** after being compressed.

FIG. **9** depicts the multilayered laminate of FIG. **8** after surface layers have been applied to the multilayered laminate.

DETAILED DESCRIPTION OF THE INVENTION

FIGS. **4**, **5**, and **6** illustrate conductive substructures in accordance with preferred embodiments of the present invention. FIG. **4** illustrates a 0S1P substructure **40**, FIG. **5** illustrates a 0S3P substructure **50**, and FIG. **6** illustrates a 2S1P substructure **60**. The 0S1P substructure **40**, the 0S3P substructure **50**, and the 2S1P substructure **60** are named in accordance with the nSmP notation described supra. Thus, "0S1P" connotes 0 signal planes and 1 power plane (n=0, m=1), "0S3P" connotes 0 signal planes and 3 power planes (n=0, m=3), and "2S1P" connotes 2 signal planes and 1 power plane (n=2, m=1). Multilayered laminates in accordance with the present invention include stacked substructures which may include any or all of the 0S1P, 0S3P, and 2S1P substructures.

In FIG. **4**, the 0S1P substructure **40** comprises a power plane **41**. The power plane **41** includes a continuously conductive layer **42** having a hole **43** and a hole **44**. The continuously conductive layer **42** may include, inter alia, a pure metal (e.g., copper), a metallic alloy, or a layered sandwich (e.g., a copper-Invar-copper sandwich with a sublayer of Invar sandwiched between sublayers of copper). While the continuously conductive layer **42** includes the two holes **43** and **44**, the continuously conductive layer **42** may include any number of holes or no hole.

The 0S1P substructure **40** of FIG. **4** may be generated in accordance with preferred embodiments of the present invention as follows. Initially, the continuously conductive layer **42** would be provided as a sheet of the conductive material. Then the holes **43** and **44** may be formed in the continuously conductive layer **42**, such as by mechanical drilling, laser drilling, or photolithographically. An example of how photolithography may be used to form the holes **43** and **44** includes applying a layer of photoresist to a surface of the continuously conductive layer **42**, patterning and selectively exposing the photoresist to radiation (e.g., ultraviolet radiation) such that the photoresist is exposed only where the holes **43** and **44** are to be formed, etching away the exposed photoresist and the conductive material underneath the exposed photoresist to form the holes **43** and **44**, and stripping away the unexposed photoresist to fully expose the conductive material of the continuously conductive layer **42**. Note that a roll of the conductive material may initially replace the sheet of the conductive material of the conductive layer **42** in the aforementioned process for forming the 0S1P substructure **40**, such that a portion of the roll of the conductive material may be cut away to constitute the sheet of the conductive material, wherein the cutting away may take place either before or after the holes **43** and **44** have been formed. Also note that the power plane **41** comprises the continuously conductive layer **42** and further includes any holes (such as the holes **43** and **44**) that exist or have been formed through the continuously conductive layer **42**. The surfaces **46** and **47** of the power plane **41** may be each coated or otherwise treated with a surface layer of material such as zinc, chrome, or copper oxide to promote

adhesion of layers (e.g., dielectric layers) that will be subsequently applied to the surfaces **46** and **47**. Note that the holes **43** and **44** may be formed either before or after any subsequent application of a dielectric layer to the surfaces **46** or the surface **47**. A structure resulting from applying the dielectric layer to the surfaces **46** is called a 0S1P substructure.

In FIG. **5**, the 0S3P substructure **50** comprises an interior power plane **54**, a surface power plan **51**, a surface power plane **58**, a dielectric layer **152** between the power planes **54** and **51**, and a dielectric layer **153** between the power planes **54** and **58**. The power plane **54** includes a continuously conductive layer **55** having a hole **56** and a hole **57**, wherein the holes **56** and **57** each include dielectric material from the dielectric layers **152** and **153**. While the continuously conductive layer **55** includes the two holes **56** and **57**, the continuously conductive layer **55** may include any number of holes or no hole. The power plane **51** includes a continuously conductive layer **52** having a hole **53**. While the continuously conductive layer **52** includes the hole **53**, the continuously conductive layer **52** may include any number of holes or no hole. The power plane **58** includes a continuously conductive layer **59** having a hole **151**. While the continuously conductive layer **59** includes the hole **151**, the continuously conductive layer **59** may include any number of holes or no hole. The continuously conductive layers **52**, **55**, and **59** may each include, inter alia, a pure metal (e.g., copper), a metallic alloy, or a layered sandwich (e.g., a copper-Invar-copper sandwich with a sublayer of Invar sandwiched between sublayers of copper). The continuously conductive layers **52**, **55**, and **59** may each include the same conductive material or different conductive materials. The dielectric layers **152** and **153** each comprise a dielectric material such as, inter alia, a photoimageable dielectric (PID) material, a pure resin material, an epoxy material, and a glass-reinforced dielectric.

The 0S3P substructure **50** of FIG. **5** may be generated in accordance with preferred embodiments of the present invention as follows. Initially, the power plane **54** having the continuously conductive layer **55** (including the holes **56** and **57**) is formed in the same manner as the power plane **41** of FIG. **4** is formed, as described supra. After the continuously conductive layer **54** is formed, the dielectric layers **152** and **153** are respectively applied to opposite surfaces **154** and **155**, respectively, of the continuously conductive layer **54**. Prior to the application of the dielectric layers **152** and **153**, the opposite surfaces **154** and **155** may be each coated or otherwise treated with a surface layer of material such as zinc, chrome, or copper to promote adhesion of the dielectric layers **152** and **153** to the surfaces **154** and **155**, respectively. The dielectric material of the dielectric layers **152** and **153** fills the holes **56** and **57** during the application of the dielectric layers **152** and **153**. Then the power planes **51** and **58** may be formed by applying a sheet of a conductive material (in the form of a separate sheet or from a roll) on the dielectric layers **152** and **153**. The holes **53** and **151** in the power planes **51** and **58**, respectively, may be formed in the same manner (i.e., pholithographically with selective etching) as the holes **43** and **44** are formed in the power plane **41** as described supra in conjunction with FIG. **4**. The holes **53** and **151** may be formed in the power planes **51** and **58**, respectively, either before or after the planes **51** and **58** are applied to the dielectric layers **152** and **153**, respectively. Note that the dielectric layers **152** and **153** may initially be in a form of complete sheets or alternatively may be cut from a roll of dielectric material before or after being applied to the power plane **54**.

In FIG. **6**, the 2S1P substructure **60** comprises an interior power plane **61**, a signal plane **63**, a signal plane **65**, a dielectric layer **67** interfaced between the power plane **61** and the signal plane **63**, and a dielectric layer **68** interfaced between the power plane **61** and the signal plane **65**. The 2S1P substructure **60** also includes the plated via **69** and the plated via **161**. The power plane **61** includes a continuously conductive layer **62** having a hole **164** and a hole **165**, wherein the holes **164** and **165** each include dielectric material from the dielectric layers **67** and **68**. While the continuously conductive layer **62** includes the two holes **164** and **165**, the continuously conductive layer **62** may include any number of holes or no hole. The continuously conductive layer **62**, and the signal layers **63** and **65**, may each include, inter alia, a pure metal (e.g., copper), a metallic alloy, or a layered sandwich (e.g., a copper-Invar-copper sandwich with a sublayer of Invar sandwiched between sublayers of copper). The continuously conductive layer **62**, and the signal layers **63** and **65**, may each include the same conductive material or different conductive materials. The dielectric layers **67** and **68** each comprise a dielectric material such as, inter alia, a photoimageable dielectric (PID) material, a pure resin material, an epoxy material, and a glass-reinforced dielectric material. The 2S1P substructure **60** also includes the plated via **69** and the plated via **161**. While the 2S 1 P substructure **60** includes the two plated vias **69** and via **161**, the 2S1P substructure **60** may include any number of plated vias or no plated via. Additionally, 2S1P substructure **60** may include any number of unplated vias or no unplated via.

The 2S1P substructure **60** of FIG. **6** may be generated in accordance with preferred embodiments of the present invention as follows. Initially, the power plane **61** comprising the continuously conductive layer **62** (including the holes **164** and **165**) is formed in the same manner as the power plane **41** of FIG. **4** is formed, as described supra. After the power plane **61** is formed, the dielectric layers **67** and **68** are applied to opposite surfaces **166** and **167**, respectively, of the continuously conductive layer **62**. Prior to the application of the dielectric layers **67** and **68**, the opposite surfaces **166** and **167** may be each coated or otherwise treated with a surface layer of material such as zinc, chrome, or copper oxide to promote adhesion of the dielectric layers **67** and **68** to the surfaces **166** and **167**, respectively. The dielectric material of the dielectric layers **67** and **68** fills the holes **164** and **165** during the application of the dielectric layers **67** and **68**. Note that the dielectric layers **67** and **68** may initially be in a form of complete sheets or alternatively may be cut from a roll of dielectric material before or after being applied to the power plane **61**. Next, sheets of conductive material, which may include a conductive metal such as copper, may be applied to the surfaces **162** and **163** of the dielectric layers **67** and **68**, respectively. The signal planes **63** and **65** will be subsequently formed from said sheets of conductive material. Alternatively, the aforementioned sheets of conductive metal may be applied (e.g. coated) to the dielectric layers **67** and **68** (either in sheet or roll format) prior to applying the dielectric layers **67** and **68** to the surfaces **166** and **167**, respectively. The aforementioned sheets of conductive metal may be circuitized to form the signal planes **63** and **65** by a subtractive process that comprises a photolithographic process followed by selective etching which removes conductive metal from the sheets of conductive metal where there is to be no circuitization.

An alternative method of forming the signal planes **63** and **65** is by an additive process that eliminates use of the aforementioned sheets of conductive metal. Instead, perma-

nent or temporary photoresist layers are formed on the surfaces **162** and **163**. The photoresist is patterned and photolithographically exposed to radiation (e.g., ultraviolet radiation). Then channels are formed in the photoresist layers by selective etching. The channels are filled, such as by being plated, with an electrically conductive material (e.g., copper) that forms circuitization of the signal planes **63** and **65**. If the photoresist layers were intended to be temporary, then the remaining photoresist is removed by any method known to one of ordinary skill in the art such as by chemical etching. Regardless of the method of formation, the signal planes **63** and **65** may be formed simultaneously, in overlapping periods of time, or within distinct periods of time.

Plated vias **69** and **161** of the 2S1P substructure **60** may be formed by mechanical or laser drilling of holes through: the conductive material of the signal plane **63**, the dielectric material of the dielectric layer **67**, the dielectric material within the power plane **61**, the dielectric material of the dielectric layer **68**, and the signal plane **65**, followed by plating the holes with a conductive material. Alternatively, the plated vias **69** and **161** could be formed by mechanical or laser drilling of the holes prior to forming the signal planes **63** and **65**. An additional alternative is available if the dielectric material of the of the dielectric layers **67** and **68** includes a PID material. With the additional alternative, the plated vias **69** and **161** could be formed by patterned photoimaging and selective etching the PID material prior to forming the signal planes **63** and **65**.

The dielectric material within the 0S3P substructure **50** of FIG. **5** and within the 2S1P substructure **60** of FIG. **6**, is initially provided as uncured. The dielectric material may be cured after being applied to within the 0S3P substructure **50** or to within the 2S1P substructure **60**. The 2S1P substructure **60** of FIG. **6** may be cured, inter alia, by heating or by pressurizing followed by heating. Alternatively if the dielectric material includes PID material, then the dielectric material may be photocured (e.g., by use of ultraviolet radiation). For the 2S1P substructure **60** of FIG. **6**, the dielectric material is cured preferably before the plated vias **69** and **161** are formed.

FIG. **7** illustrates a multilayered laminate **70** that includes 0S1P, 0S3P, and 2S1P substructures, in accordance with preferred embodiments of the present invention. In particular, the multilayered laminate **70** includes the following sequentially stacked arrangement of substructures and dielectric layers: a 2S1P substructure **71**, a dielectric layer **80**, a 0S1P substructure **72**, a dielectric layer **81**, a 2S1P substructure **73**, a dielectric layer **82**, a 0S3P substructure **74**, a dielectric layer **83**, a 2S1P substructure **75**, a dielectric layer **84**, a 0S1P substructure **76**, a dielectric layer **85**, and a 2S1P substructure **77**.

Although the aforementioned sequentially stacked substructures **71–77** and dielectric layers **80–85**, will be subsequently subjected to compressive stresses, they have not yet been subject to said compressive stresses. Accordingly, the sequentially stacked substructures **71–77** and dielectric layers **80–85** have intervening void regions **90–99** as follows. The void region **90** intervenes between the 2S1P substructure **71** and the dielectric layer **80**. The void region **91** intervenes between the dielectric layer **80** and the 0S1P substructure **72**. The void region **92** intervenes between the 0S1P substructure **72** and the dielectric layer **81**. The void region **93** intervenes between the dielectric layer **81** and the 2S1P substructure **73**. The void region **94** intervenes between the 2S1P substructure **73** and the dielectric layer **82**. The void region **95** intervenes between the dielectric layer **82** and the 0S3P substructure **74**. The void region **96** intervenes between the 0S3P substructure **74** and the dielectric layer **83**. The void region **97** intervenes between the dielectric layer **83** and the 2S1P substructure **75**. The void region **98** intervenes between the 2S1P substructure **75** and the dielectric layer **84**. The void region **99** intervenes between the dielectric layer **84** and the 0S1P substructure **76**. The void region **100** intervenes between the 0S1P substructure **76** and the dielectric layer **85**. The void region **101** intervenes between the dielectric layer **85** and the 2S1P substructure **77**. Note that void space also exists in: a plated via **102** of the 2S1P substructure **71**, holes **103** and **104** in the 0S1P substructure **72**, a plated via **105** of the 2S1P substructure **73**, a plated via **106** of the 2S1P substructure **75**, holes **107** and **108** in the 0S1P substructure **76**, and a plated via **109** of the 2S1P substructure **77**.

The 0S1P substructures **72** and **76** of the multilayered laminate **70** in FIG. **7** have the same properties and features as were described supra in conjunction with FIG. **4** for the 0S1P substructure **40**. The 0S3P substructure **74** of the multilayered laminate **70** in FIG. **7** has the same properties and features as were described supra in conjunction with FIG. **5** for the 0S3P substructure **50**. The 2S1P substructures **71** , **73**, **75**, and **77** of the multilayered laminate **70** in FIG. **7** have the same properties and features as were described supra in conjunction with FIG. **6** for the 2S1P substructure **60**.

The particular arrangement of 0S1P, 0S3P, and 2S1P substructures in FIG. **7** is merely illustrative of the numerous possible arrangements. Generally, a multilayered laminate of the present invention may include any number and arrangements of 0S1P, 0S3P, and 2S1P substructures. Any or all of 0S1P, 0S3P, and 2S1P substructures may be present in the multilayered laminate. A multilayered laminate that comprises a 0S1P substructure and a 0S3P substructure, with no internal signal layers, may be useful in a power distribution system or in a structure with all circuitization on the external, exposed surfaces of the multilayered laminate. Note that a multilayered laminate may additionally include conventional substructures such as the 0S2P substructure **10**, the 2S0P substructure **20**, and the 1S1P substructure **30**, described supra in conjunction with FIG. **1**, FIG. **2**, and FIG. **3**, respectively.

FIG. **8** illustrates the multilayered laminate **70** of FIG. **7** after being compressed under an elevated temperature, such as by pressurization in a lamination press under a pressure preferably between about 100 psi and about 700 psi at a temperature preferably between about 180° C. and about 210° C. The compression and heating of the dielectric material of the dielectric layers **80–85** causes said dielectric material to flow. The heating of the dielectric material of the dielectric layers **80–85** cures said dielectric material. The compression of the multilayered laminate **70** eliminates the void regions **91–101** which were discussed supra in conjunction with FIG. **7**. As a result of the compression, the dielectric material of the dielectric layers **80–85** fills out the prior void spaces between, and insulatively separates, each pair of successive substructures of the substructures **71–77** as follows. The dielectric material of the dielectric layer **80** fills the space between, and insulatively separates, the 2S1P substructure **71** and the 0S1P substructure **72**. The dielectric material of the dielectric layer **81** fills the space between (and insulatively separates) the 0S1P substructure **72** and the 2S1P substructure **73**. The dielectric material of the dielectric layer **82** fills the space between, and insulatively separates, the 2S1P substructure **73** and the 0S3P substructure **74**. The dielectric material of the dielectric layer **83** fills

the space between, and insulatively separates, the 0S3P substructure **74** and the 2S1P substructure **75**. The dielectric material of the dielectric layer **84** fills the space between, and insulatively separates, the 2S1P substructure **75** and the 0S1P substructure **76**. The dielectric material of the dielectric layer **85** fills the space between, and insulatively separates, the 0S1P substructure **76** and the 2S1P substructure **77**.

From the aforementioned flow and cure of dielectric material, the dielectric material of the dielectric layers **80–85** fill out the space in the plated vias and power planes as follows. The plated via **102** of the 2S1P substructure **71** is filled with dielectric material from the dielectric layer **80**. The holes **103** and **104** in the 0S1P substructure **72** are filled with dielectric material from the dielectric layers **80** and **81**. The plated via **105** of the 2S1P substructure **73** is filled with dielectric material from the dielectric layers **81** and **82**. The plated via **106** of the 2S1P substructure **75** is filled with dielectric material from the dielectric layers **83** and **84**. The holes **107** and **108** in the 0S1P substructure **76** are filled with dielectric material from the dielectric layers **84** and **85**. The plated via **109** of the 2S1P substructure **77** is filled with dielectric material from the dielectric layer **85**.

After the multilayered laminate **70** has been compressed, a plated through hole (PTH) **140** may be formed through the multilayered laminate **70**. The PTH **140** may be formed by any method known to one of ordinary skill in the art, such as mechanical or laser drilling. Although FIG. **8** does not explicitly show the PTH **140** as being electrically (i.e., conductively) coupled to any of the substructures **71–77**, the PTH **140** and the substructures **71–77** may be formed such that the PTH **140** conductively contacts some or all of the substructures **71–77**. Thus the PTH **140** may be used to provide electrical coupling among or between some or all of the substructures **71–77**. Additionally, the PTH **140** may be conductively coupled to electronic structures external to the multilayered laminate **70** (e.g., a chip) as will be discussed infra in conjunction with FIG. **9**.

The surface layers **120** and **130**, if present, may be applied to the multilayered laminate **70** as will be shown infra in conjunction with FIG. **9**. The surface layer **120** includes a dielectric sheet **122**, a microvia **124**, a microvia **126**, and a microvia **128**, such that the microvias **124**, **126**, and **128** are within the dielectric sheet **122**. The microvias **122**, **124**, and **126** each have a plated layer of conductive material (e.g., copper). The surface layer **130** includes a dielectric sheet **132**, a microvia **134**, a microvia **136**, and a microvia **138**, such that the microvias **134**, **136**, and **138** are within the dielectric sheet **132**. The microvias **134**, **136**, and **138** each have a plated layer of conductive material (e.g., copper). The surface layers **120** and **130** may serve to effectuate electrically conductive coupling between the multilayered laminate **70** and external electronic structures. For example, the surface layer **120** may conductively couple a semiconductor chip to the multilayered laminate **70** by use of some or all of the microvias **124**, **126**, and **128**, as discussed infra in conjunction with FIG. **9**. As another example, the surface layer **130** may conductively couple a solder ball of a ball grid array (BGA) to the multilayered laminate **70** by use of some or all of the microvias **134**, **136**, and **138**. The dielectric sheets **122** and **132** may include any dielectric material having structural and insulative properties that support said conductive coupling between the multilayered laminate **70** and the external electronic structures. The dielectric material within the dielectric sheets **122** and **132** preferably includes a resin comprising an allylated polyphenylene ether (APPE). A particularly useful APPE is an APPE resin coated on a copper foil, made by the Asahi Chemical Company of Japan and identified as Asahi product number PC**5103**. Alternatively, the dielectric material within the dielectric sheets **122** and **132** may include a photoimageable dielectric or a resin-coated copper foil. Although the surface layers **120** and **130** are each shown in FIG. **8** to include three microvias, the surface layers **120** and **130** may each include any number of microvias, or no microvia. The number of microvias included within the surface layer **120** may be unrelated to the number of microvias included within the surface layer **130**. In addition to having microvias, the surface layers **120** and **130** may each include surface circuitization lines.

FIG. **9** illustrates FIG. **8** after the surface layers **120** and **130** have been applied to the multilayered laminate **70** by any method that is compatible with the particular dielectric material used in the dielectric sheet **122** and **132**, respectively. For example, the surface layers **120** and **130**, if including the allylated polyphenylene ether (APPE) that is initially coated on a copper foil such as the Asahi resin PC**5103** (discussed supra), may be applied to the multilayered laminate **70** by pressurization in a range of about 1000 psi to about 2000 psi at an elevated temperature between about 180° C. and about 210° C. for a time of at least about 90 minutes. The pressurization and elevated temperatures causes the APPE resin to flow and become cured, resulting in application of the surface layers **120** and **130** to the multilayered laminate **70**. After the pressurization, the copper foils may be left intact, or removed in any manner known to one of ordinary skill in the art, such as by etching.

Although the preceding discussion described how the surface layers **120** and **130** may be applied to the multilayered laminate **70** after to the multilayered laminate **70** has been compressed as described supra in conjunction with FIG. **7**, the surface layers **120** and **130** may alternatively be applied to the multilayered laminate **70** prior to the compression of the multilayered laminate **70** as follows. The dielectric sheets **122** and **132** (without added metalization or circuitization) of the surface layers **120** and **130**, respectively, are placed on the multilayered laminate **70**. When the multilayered laminate **70** is subsequently compressed by use of a compressive force, the dielectric sheets **122** and **132** are subject to the compressive force and are thus caused to adhere to the multilayered laminate **70**. After the compression, the microvias **124**, **126**, **128**, **134**, **136**, and **138** (and associated plating) may be formed in the surface layers **120** and **130** as shown in FIG. **8** and discussed supra in the text that describes FIG. **8**. Also after the compression, the plated through hole **140** may be formed as discussed supra in conjunction with FIG. **8**. The plated through hole **140** thus formed would pass through the surface layer **120**, the multilayered laminate **70**, and the surface layer **130**.

The microvias **124**, **126**, and **128** are formed in the surface layer **120** after the surface layer **120** has been applied to the multilayered laminate **70**. Similarly, the microvias **134**, **136**, and **138** are formed in the surface layer **130** after the surface layer **130** has been applied to the multilayered laminate **70**. The microvias **124**, **126**, and **128**, as well as the microvias **134**, **136**, and **138**, may be formed by any method known to one of ordinary skill in the art, such as by laser drilling into the dielectric sheet **122** down to the conductive metalization on the signal layer **120** to form a microvia, followed by electroless plating of metal (e.g., copper) on seeded surfaces (e.g., palladium seeded surfaces) of the microvia to form an electroless layer of the metal. After the electroless plating, the metal (e.g., copper) is electroplated over the electroless layer to form the plated layer of each of microvias **124**, **126**, **128**, **134**, **136**, and **138**.

In FIG. **9**, an electrical device **145** (e.g., a semiconductor chip) has been coupled to the multilayered laminate **70** by solder contact members **146**, **147**, and **148**. The solder contact members **146**, **147**, and **148** are conductively coupled to the solder interfaces **185**, **187**, and **189** within the microvias **124**, **126**, and **128**, respectively. The plated layers **125**, **127**, and **129** of the microvias **124**, **126**, and **128**, respectively, are conductively coupled to the multilayered laminate **70** at the 2S1P substructure **71** and at the plated through hole **140**. The solder contact members **146**, **147**, and **148** may each include, inter alia, a Controlled Collapse Chip Connection (C4) solder ball. If the surface layer **120** is not present, then the electrical device **145** may be conductively coupled directly to the multilayered laminate **70** at the 2S1P substructure **71** and at the plated through hole **140**.

While preferred and particular embodiments of the present invention have been described herein for purposes of illustration, many modifications and changes will become apparent to those skilled in the art. Accordingly, the appended claims are intended to encompass all such modifications and changes as fall within the true spirit and scope of this invention.

We claim:

1. An electrical structure, comprising: a multilayered laminate that includes a plurality of substructures, wherein a dielectric material of a dielectric layer insulatively separates each pair of successive substructures, and wherein the plurality of substructures includes a 0S1P substructure and a 2S1P substructure.

2. An electrical structure, comprising: a multilayered laminate that includes a plurality of substructures, wherein a dielectric material of a dielectric layer insulatively separates each pair of successive substructures,and wherein the plurality of substructures includes a 0S3P substructure and a 2S1P substructure.

3. An electrical structure, comprising: a multilayered laminate that includes a plurality of substructures, wherein a dielectric material of a dielectric layer insulatively separates each pair of successive substructures, and wherein the plurality of substructures includes a 0S1P substructure, a 0S3P substructure, and a 2S1P substructure.

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